

the free layer and reference layer over the curved regions to produce the curved portions. Read and write wires may also be formed in portions of the etched grooves.

[0007]The above described embodiments of the present invention substantially improve upon the prior art by providing magnetic memory cells that exhibit magnetic anisotropy, substantially uniform magnetic coercivities and are relatively easy and inexpensive to construct. In addition, the coercivity of a magnetic memory cell constructed in accordance with the above discussed embodiments is independent of the thickness of the memory cell. Thus, dense arrays of magnetic memory cells may be constructed in accordance with the preferred embodiments of the present invention without substantially decreasing their volume and, thereby, increasing the likelihood of thermally induced errors. Thus, the present invention is particularly well suited for use in applications where it is desirable to produce as small of a magnetic memory cell as possible.

15 BRIEF DESCRIPTION OF THE DRAWINGS

1a-1c
[0008]FIGS. ~~1(a-c)~~ are illustrations of a magnetic random-access memory cell constructed according to a preferred embodiment of the present invention;

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